Three-dimensional imaging of material functionality through nanoscale tracking of energy flow

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The ability of energy carriers to move within and between atoms and molecules underlies virtually all biochemical and material function. Understanding and controlling energy flow, however, requires observing it on ultrasmall and ultrafast spatiotemporal scales, where energetic and structural roadblocks dictate the fate of energy carriers. We therefore developed a universal, non-invasive optical scheme that leverages interferometric scattering to track tiny changes in material polarizability created by energy carriers. Our approach enables mapping energy transport trajectories in four dimensions of spacetime with few-nanometer precision and directly correlating them to material morphology. We visualize exciton, charge, and heat transport in polyacene, silicon and perovskite semiconductors and elucidate, in particular, how grain boundaries impact energy flow through their lateral- and depth-dependent resistivities. We reveal new strategies to interpret energy transport in disordered environments that will direct the design of defect-tolerant materials for the semiconductor industry of tomorrow.

Energy flow is a ubiquitous phenomenon, central to the function of all biological, chemical and material systems. Elucidating how distinct macroscopic system functions emerge from different structural arrangements of atoms and molecules is a longstanding goal of scientific research, and one that necessarily relies on understanding how energy is transduced and transported between the system’s building blocks. Materials science, for example, is undergoing a revolution with a recent burst of new high-performing semiconductors made from a vast diversity of molecular building blocks that can be readily tuned for specific functions. Nevertheless, a fundamental understanding of why some semiconductors perform better than others remains elusive, inhibiting the rational design of future materials. The difficulty in gaining such predictive power is compounded by often-encountered nanoscale spatio-energetic disorder, manifested in defects, impurities, and grain boundaries (GBs), that give rise to complex and spatio-temporally heterogeneous energy transport behavior. Elucidating how the microscopic details of a material relate to its emergent optoelectronic function will therefore require the ability to individually, systematically, and easily correlate nanoscale structure to energy flow across a wide range of systems.

Resolving how energy flow is impacted by material structure and spatio-energetic disorder requires tracking energy carriers over a wide spatiotemporal range, typically nanometers to microns and picoseconds to milliseconds, and directly correlating the measurement to material morphology. This correlation notwithstanding, powerful spatiotemporally resolved approaches have recently been developed to visualize nanoscale energy flow using photoluminescence, transient absorption, or electron scattering as contrast mechanisms. They achieve femtosecond time resolution, large dynamic range, chemical specificity, and excellent spatial sensitivity. Nevertheless, in their current implementations, most of these methods track only a subset of energy carrier types, and rely on samples having specific optical or electronic properties, such as being absorbing yet low optical density, having large Stokes
shifts and appreciable emission, or being resistant to electron beams. They also currently measure energy flow in two dimensions only, and most acquire a single image pixel at a time. These constraints limit the variety of samples and fundamental processes that can be studied. Overcoming these challenges, we developed an approach that leverages elastic scattering, a universal optical interaction, to directly track any type of energy carrier in 3 spatial dimensions, irrespective of its optical properties, as it moves through any material on picosecond to millisecond timescales. Importantly, this approach enables simultaneous imaging of the nano-to-microscale morphological features that define the spatioenergetic landscape of the material, providing the much sought after in situ structure-function correlations.

Our approach makes use of the exquisite sensitivity of interferometric scattering microscopy (iSCAT). iSCAT provides three dimensional (3D) imaging capability through phase contrast and enables label-free detection of extremely weak scatterers, down to single molecules. Whereas iSCAT involves interferometrically detecting elastically scattered light from sample features due to local variations in polarizability (index of refraction), here we open up a wide range of possibilities to instead probe the presence and time evolution of photogenerated energy carriers. To employ iSCAT as a probe in a time-resolved (stroboscopic) pump-probe measurement, we first introduce a short pump light pulse to generate a localized collection of energetic carriers that effectively act as point scatterers in the sample by modifying local polarizability; subsequently the large-area iSCAT probe pulse interrogates at controllable time delays the change in the spatiotemporal elastic scattering profile of the sample induced by the pump pulse (Figure 1a and Supplementary Sections 1-2). Indeed, molecular excited states as well as crystal lattices in the presence of energy carriers typically possess vastly different polarizabilities compared to their unexcited counterparts, providing an easily resolved molecular-scale indicator of different photoexcitations and of their spatiotemporal evolution. Stroboscopic iSCAT (stroboSCAT) thus solves many of the aforementioned challenges by affording non-invasive, far-field probing through thick (opaque) or thin (transparent) samples that do not need to be emissive; on- or off-resonant probing of a material’s imaginary or real dielectric response; high 3D spatial and temporal resolution, sensitivity and dynamic range; simultaneous imaging of energy carriers and material morphology; and rapid and robust data acquisition through wide-field imaging, with each dataset in this article employing <15 minute acquisition times. As we show below, these unique attributes enable detailed and model-free structure-function correlations of a broad range of materials, precisely pinpointing the origin of functional heterogeneity in disordered semiconductors.
Figure 1. Visualizing semiconductor exciton, charge and heat transport across four orders of magnitude in space and time. (a) stroboSCAT setup. A confocal pump (306 nm diameter, λ = 440 nm) and widefield probe (8 µm diameter, λ = 635 nm) are overlapped in the sample. Both probe light scattered by the sample and reflected at the sample-substrate interface are imaged on the camera (CMOS). Full details in Supplementary Sections 1-6. (b) Example stroboSCAT dataset for a MAPbBr$_3$ single crystal, showing charge carriers diffusing as a function of pump-probe time delay. The pump-injected carrier density is 2 x 10$^{18}$ cm$^{-3}$ and the probe is off-resonant with both ground and excited-state absorption. All stroboSCAT plots are generated by taking the difference between pump$_{ON}$ and pump$_{OFF}$ raw images, normalized to the raw pump$_{OFF}$ image. Scale bar 1 µm. The spatiotemporal population distribution along the horizontal spatial axis is plotted in c, along with 1D Gaussian profiles extracted at 0 and 1 ns pump-probe delay. (d) Charge, exciton, or heat distributions vs time measured for a range of semiconductors (Supplementary Section 7). Error bars represent the 95% confidence intervals from Gaussian fits. (e) Diffusivities extracted from linear fits of the data in (d).

We use stroboSCAT to visualize energy flow in a wide range of semiconductors, demonstrating its capability over four orders of magnitude in space and time, on both neutral and charged excitations migrating through both ordered and disordered organic, organic-inorganic, and inorganic semiconductors. Before focusing on disordered semiconductors, we illustrate the general principles behind imaging diffusive behavior using stroboSCAT with an example in an ordered semiconductor: Figures 1b,c display the spatial profile of charge carriers as a function of pump-probe delay in a methylammonium lead bromide (MAPbBr$_3$) perovskite single crystal. In this simple example, the diffusivity $D$ for the charge carriers can...
be modelled from the Gaussian distribution variance of the scattering profile with time, $2Dt = \sigma^2(t) - \sigma^2(0)$ (Supplementary Section 3). The achievable spatial precision, ±2 nm for a 10 minute measurement, is not limited by diffraction but rather by the lowest achievable distinction between the widths of two Gaussian distributions, which depends on the shot noise-limited signal-to-noise ratio$^{3,14}$. Figures 1d,e summarize similar analyses on a variety of semiconductors using the same setup configuration to image heat, neutral bound pairs of charges (excitons), and free charge carrier diffusion. Since each type of energy carrier changes the local polarizability of the medium in a different way, the magnitude and sign of the stroboSCAT contrast permits clear distinction of the multiple types of energy carriers that may co-exist and co-evolve, as in silicon (Figure S4).

Our results closely match published values for the materials whose energy diffusivities have previously been determined$^{28-32}$, confirming the viability of our approach. One notable observation in Figures 1d,e is that carrier diffusivities in MAPbBr$_3$ are reduced more than fourfold in disordered polycrystalline films compared to single crystals. Nevertheless, the impact of disorder and in particular GBs on energy flow can be non-trivial, depending greatly on their type, size, distribution and composition. We demonstrate below that stroboSCAT can directly image and morphologically correlate energy flow up to, within and across these energetic obstacles, using two classes of emerging semiconductors as case studies. Our results and corroborating simulations reveal that carrier trajectories are governed by highly anisotropic paths of least resistance, precluding the viability of diffusive models extracted from bulk measurements and calling for new ways to interpret and quantify energy flow in disordered environments.

We first explore the effect of low-curvature domain interfaces on exciton migration in polycrystalline 6,13-bis(triisopropylsilylethynyl)pentacene (TIPS-Pn) films, to understand how crystalline boundaries and lattice misorientations affect energy flow. TIPS-Pn is a promising singlet-fission sensitizer for hybrid solar panels and represents an archetypal system to study energy transport in π-stacked molecular crystals (Figure 2a)$^{33,34}$. We prepare films of TIPS-Pn containing few-micron-sized crystalline domains separated by straight interfaces with crystallinity maintained up to the interfacial region. In Figure 2b, iSCAT images at two different probe field polarizations display two orthogonally-oriented crystalline domains (light vs dark) separated by such interfaces. Exciton migration imaged by stroboSCAT within a grain (Figure 2c-e) shows that at early time delays, the migration is non-linear, lending support to previous reports that attribute this behavior to the interchange between fast-diffusing singlet and slow-diffusing triplet pair excitations$^{35}$. Beyond 5 ns, the linear diffusion that we observe at $D=0.003$ cm$^2$/s (Figure S12) is consistent with the common interpretation of free triplet migration$^{33,35}$.

The key new finding enabled by stroboSCAT is the degree to which individual GBs hinder exciton transport in molecular crystals, and in particular that the extent of this hindrance varies widely from GB to GB. The narrow wedge-shaped central domain in this example provides an interesting opportunity to systematically quantify the effect of domain confinement by interfaces on exciton migration (Figure 2d). Population distribution expansion along the fast diffusion axis at red, orange, and yellow spots highlighted in Figures 2b,d are plotted in Figure 2e. A clear difference is observed between the bulk crystalline domain (red) and the most confined spot (yellow), with interfaces severely hindering exciton transport, slowing it approximately four-fold. Transport at the partially-confined area (orange) can be accurately modeled by a linear combination of free migration up to 3 ns (overlapping orange and red curves) and confined migration thereafter (orange curve parallels yellow curve), indicating a clear transition from bulk-like to slower
transport when reaching an interface. We measured exciton migration in 15 different grains and at 17 different GBs and found that (i) exciton transport is always slower at GBs than in grains (Figure 2f inset); and (ii) transport speed is consistent in all measured grains, whereas transport at GBs is highly variable, as indicated by the normalized distribution of initial \((t=0)\) diffusivities in Figure 2f. Indeed, interface formation kinetics, degree of lattice misorientations, and void and impurity concentrations will give rise to a wide range of transport behavior at different interfaces. The high-throughput and correlative stroboSCAT measurements of exciton migration over nanometer length scales provides the ability to investigate energy transport properties in situ for each interface and surrounding crystal domains and to correlate these to their specific morphologies.

Figure 2: Morphology-dependent exciton transport in TIPS-Pentacene. (a) crystal structure of TIPS-Pn. (b) iSCAT images at different polarizations (pol) showing two orthogonally-oriented crystal domains. These images are bandpass-filtered to remove diffraction fringes near interfaces (Figure S8). (c) stroboSCAT images at 0 and 8 ns time delay in a crystalline grain (red spot in B), displaying anisotropic diffusion with six-fold faster transport along the \(\pi\)-stacked (red) axis of the crystal (Figure S9). (d) Schematic of exciton diffusion behavior at three different spots – intra-grain (red), confined (yellow), and intermediate transport scenarios (orange). (e) Corresponding population expansion dynamics along the fast diffusion axes. The pump is circularly polarized and the probe polarization is chosen to avoid contrast bias across grains (Figure S10-S11). (f) Spot-to-spot variability of initial diffusivity \(D_0\), determined from the fitting function \(f(t)=2D_0t^\alpha\) with \(\alpha\) being a free parameter, for intra-grain and GB-confined scenarios. Peak fluence is 140 \(\mu\)J/cm\(^2\) (Figure S12). Scale bars are all 1 \(\mu\)m.
Although large crystalline domains separated by abrupt interfaces provide a systematic and controllable environment to test the effects of crystalline mismatches on energy transport, a more commonly encountered morphology in polycrystalline semiconductors consists of sub-to-few-micron-sized grains. In these materials, energy carriers almost inevitably encounter GBs during their lifetimes. GBs thus significantly impact bulk-averaged measures of energy flow such as charge mobility and recombination\textsuperscript{37,38}. There is, however, little consensus on the mechanistic effect of GBs on the functional properties of a wide range of semiconductors. Nowhere is the debate currently more salient than with metal-halide perovskites; despite impressive performance improvements for solar energy, display, and detector technologies, many questions remain regarding the role of GBs on charge carrier extraction efficiencies and degradation pathways\textsuperscript{39–48}. In particular, despite numerous studies suggesting GBs have large trap densities, act as recombination and degradation centers, and impede carrier transport, the efficiency and stability of perovskite photovoltaic devices do not necessarily scale favorably with grain size.\textsuperscript{49} The primary difficulty in resolving these paradoxes lies in elucidating to what extent the functional impacts of GBs locally deviate from bulk-averaged metrics. This challenge is exacerbated by the vast diversity of preparation protocols for polycrystalline metal halide perovskites, leading to radically different GB densities and material properties\textsuperscript{50}. We nevertheless show next that the unique 3D imaging capabilities and large temporal dynamic range of stroboSCAT enable tracking of carriers as they structurally and functionally trace the paths of least resistance through different polycrystalline lead halide perovskite films, providing systematic and individualized detail on the location and effect of traps, the lateral- and depth-dependent conductive properties of GBs, and the resulting spatiotemporal anisotropy of charge transport as a function of material morphology and heterogeneity.

The stroboSCAT time series in Figure 3a illustrates differences in charge carrier diffusivity extracted for three polycrystalline methylammonium lead iodide (MAPbI\textsubscript{3}) films prepared from different precursors using widespread preparation protocols that lead to different grain sizes (Supplementary Section 4). Because these samples are strongly emissive, we also display the correlated steady-state widefield emission pattern arising from the recombination of electrons and holes following pump excitation\textsuperscript{43} in Figure 3b, obtained in the same instrument (Supplementary Section 1). The good correspondence between widefield emission and stroboSCAT images at late time delays confirms that the full extent of carrier migration is captured by stroboSCAT. On average, films with smaller grains exhibit slower lateral carrier transport, confirming that GBs negatively affect inter-grain carrier transport. From the data in Figure 3a we extract 2D lateral diffusion lengths azimuthally- and time-averaged over the first 2 ns of 180 nm, 200 nm, and 700 nm for films made respectively with PbAC\textsubscript{2}, PbI\textsubscript{2} and PbCl\textsubscript{2} precursors.

Importantly, in the largest-grain sample in Figure 3a, the sign of the stroboSCAT contrast can reverse from negative to positive. By correlating stroboSCAT measurements to structural maps in the same field of view in Supplementary Section 8, we show that these contrast flips occur only at GBs, as illustrated in Figure 3c. We rule out that the contrast flips arise from a change in carrier density, scattering amplitude or heat, as we do not observe these sign flips in any other region when varying the pump fluence over four orders of magnitude. We therefore attribute these contrast-flips to a change in the phase of the interferometric cross-term combining the reflected and scattered fields (Supplementary Section 2). The cross-term phase depends linearly on the depth of the scattering object with respect to the substrate, providing a direct measure of the axial position of the scatterer\textsuperscript{21}. These stroboSCAT measurements therefore suggest that as a carrier encounters a GB, the path of least resistance leads deeper into the film rather than across the GB.
Nevertheless, as illustrated in Figure 3c, once carriers have migrated deeper into the film, GB crossing into a neighboring grain becomes possible. Our findings therefore explain why recent conductive atomic force microscopy on MAPbI$_3$ films indicated infinite GB resistance at the film surface but that, somehow, carriers still migrate to adjacent grains$^{16}$.

**Figure 3.** Heterogeneous charge carrier transport in polycrystalline MAPbI$_3$. (a) stroboSCAT time series on three MAPbI$_3$ samples prepared from different precursors, and (b) corresponding widefield emission images from confocal excitation. Grain sizes are measured using atomic force microscopy (Figure S13). 2D diffusion lengths $L_{D,\text{avg}} = \sqrt{4D\tau}$ are azimuthally-averaged and are calculated over the first 2 ns only, during which $D$ is approximately linear. Normalized stroboSCAT contrast is represented in greyscale with black (white) representing the most negative (positive) value. The signals do not depend on pump or probe polarization. Scale bar is 1 µm. Peak carrier density is $1.5 \times 10^{18}$ cm$^{-3}$. (c) Representative 3D carrier paths (blue) extracted from phase-sensitive stroboSCAT images for the PbCl$_2$ precursor film. The shading is used to indicate depth-dependent positive vs negative contrast (see Figure S18c). (d) Experimental and simulated stroboSCAT data using time-propagated finite element analysis of carrier migration along the line cut indicated by the horizontal red line in (c), showing quantitative agreement. The GB positions used in the simulation are shown in the side view of panel (c). GBs in the simulations are parametrized with
depth-dependent resistivities. All simulation results are convolved with the imaging system’s point spread function. Additional details and datasets are provided in Figures S14-S20. We corroborate our interpretation of the contrast flips by time-propagating finite element simulations of carrier diffusion in heterogeneous MAPbI₃ films with a simple model. Details of the simulations are provided in Supplementary Section 8. Briefly, a 2D x-z slice of the film is employed, with GBs positioned at the locations illustrated in Figure 3c. The GBs are parametrized by resistivities that are infinite at the film surface and that rapidly drop as a function of depth. The results for the four time delays in Figure 3a are plotted in Figure 3d. We achieve excellent agreement for these data and also for additional datasets shown in Supplementary Section 8, where structural maps in the same field of view are used to further support our interpretation. These agreements enable a quantitative picture of the 3D carrier pathways in these films: GBs indeed act as impassable walls at the film surface, directing carriers deeper into the film. To best match the experiment, the GB resistivity profile approaches nearly intra-grain resistivity within ~40-80 nm of the film surface. Carriers below these depths are therefore able to cross into neighboring grains. Within grains, unimpeded 3D migration quickly leads to uniform carrier distributions. Since stroboSCAT is most sensitive to carriers located near the surface (Figure S18c), where the contrast is negative, we are able to clearly distinguish between grains (negative contrast) and GBs (positive contrast). This unique axial sensitivity afforded by phase contrast therefore provides a comprehensive 3D picture of both the morphological and functional properties of these materials.

To further illustrate the rich information available from stroboSCAT, and to gain a more generalized understanding of the influence of structural heterogeneity on energy transport, we present a set of general analyses that systematically quantify the degree of functional heterogeneity in these samples. Figure 4a plots the initial angle-resolved charge carrier lateral diffusivity for MAPbI₃ prepared with the PbCl₂ precursor, which ranges from 0.1 cm²/s to 1.1 cm²/s. The time dependence of lateral carrier motion along each of the four color-coded directions in Figure 4a is depicted in Figure 4b. The terracing observed in the time dependence illustrates how GB encounters appear to temporarily halt lateral energy flow, even though intra-grain transport can be as high as 1.3 cm²/s. Strikingly, the final plateau in population expansion occurs within several ns, indicating that a large fraction of carriers cease to diffuse on time scales much shorter than the average carrier recombination time (379 ns, Figure S14). This termination indicates that at these fluences the carrier density decreases on a few-ns timescale to below the material’s trap-state density. Furthermore, it suggests that some traps do not act as recombination centers, but may instead be hole and/or electron-selective. This feature of our analysis emphasizes the importance of tracking carriers until diffusion terminates, rather than extrapolating from the initial constant diffusion through to the carrier lifetimes, which would falsely imply an average diffusion length in this sample of ~10 µm instead of ~1 µm.
Figure 4. Quantifying spatial and temporal carrier transport heterogeneity in polycrystalline MAPbI$_3$ (a) Angle-dependent diffusivities averaged over the first 2 ns for the PbCl$_2$ precursor data shown in Figure 3a. (b) Time-dependent diffusion for four representative azimuthal angles color-coded in panel (a). (c) Population expansion for the fastest azimuthal trajectory for each dataset from Figure 3a. (d) Distribution of diffusivities over 20 radial trajectories for perovskite samples prepared from three different precursor solutions.

Figure 4c compares the fastest carrier transport trajectory in each of the three perovskite samples from Figure 3. Transport in the PbI$_2$ precursor film (red) is relatively slow before a fraction of carriers find a way to cross into a larger grain, where weaker confinement by GBs permits diffusivities approaching the average intra-grain diffusivity in PbCl$_2$ precursor films (orange). At longer times the slope flattens, indicating the carrier population has now diffused throughout the larger grain. In the PbAC$_2$ precursor film (black) the diffusion appears to proceed at a constant, slow rate that represents an average of intra- and inter-grain transport due to the small grain size. The variation among and within different samples is summarized in Figure 4d by plotting the distribution of diffusivities along 20 different azimuthal directions for each precursor dataset. Clearly, the distribution progressively broadens and shifts to larger values as grain size increases. As we learnt from a similar analysis for exciton diffusion in TIPS-Pn (Figure 2f), where intra-grain transport was homogeneous while transport at GBs varied greatly, the large degree of transport variation in large-grain samples can be primarily attributed to a large variability in GB conductance combined with the low GB-encounter rate.
Overall, in applying stroboSCAT to MAPbI₃, we demonstrate that it provides the microscopic reasons for macroscopic transport behavior and its variability: we use unique nanoscale axial – in addition to transverse – sensitivity to directly image how carriers preferentially cross GBs beneath the film surface. These measurements confirm that GBs slow down lateral carrier transport (Figure 3a), show that their resistivity is greater at the film surface than in the bulk, and directly quantify their depth-dependent resistivity (Figure 3c, d). By measuring multiple regions and different films, we reveal that each GB has its own conductivity profile, leading to inter-grain energy carrier flow patterns that are highly anisotropic both axially and laterally (Figure 4, Figures S15-16). Finally, we use stroboSCAT’s large spatiotemporal dynamic range to find that diffusion can terminate significantly earlier than recombination occurs, precluding a direct relationship between diffusion length and diffusivity (Figure 4b). Based on the 3D behavior of carriers that we image, we hypothesize that the anisotropic driving forces near GBs axially bias carrier transport, helping direct carriers toward extraction layers. This biasing could enable some smaller-grain films to counterintuitively outperform larger-grain counterparts in photovoltaic efficiencies despite the presence of more potentially deleterious GBs.

Establishing the fundamental relationship between microscopic structural motifs and how energy flows through them is a longstanding multiscale challenge that has remained unresolved. In response, we devised a highly accessible and high-throughput strategy to measure energy flow in situ that is universally applicable to different energy forms and material properties. Benefiting from the high 4D spatiotemporal resolution, sensitivity, and dynamic range of stroboSCAT, we demonstrated tracking of energy carrier trajectories through heterogeneous environments with few-nm precision, enabling direct correlation of the structure and functional connectivity in a wide range of semiconductors. We envision that stroboSCAT will impact the study of energy materials well beyond the scope of this present work. At a fundamental level, the polarizability contrast obtained from stroboSCAT could be used as a direct indicator of how coupling strengths between an energy carrier and the surrounding matrix evolve as a function of space and time, providing information on, for example, electron-phonon coupling and polaron formation and how these processes affect energy migration. Improvements in the rapidly developing sectors of detector technology, microscope stabilization, and tunable laser sources could enable stroboSCAT to reach the ultimate sensitivity limits required to track a single energy carrier. Finally, using scattering as a contrast mechanism enables a comprehensive range of processes - not only energy flow but also the transport of chemical species or ions - to be studied with the same level of detail and could shed light on catalytic cycles and chemical energy storage. Recent experiments showing the potential of iSCAT for cell imaging suggests that even many of the ultrafast dynamic processes that govern biological function, such as photosynthesis and neural signaling, could be revealed in live samples using stroboscopic interferometric scattering microscopy.

References and Notes


Acknowledgements: This work has been supported by STROBE, A National Science Foundation Science & Technology Center under Grant No. DMR 1548924. Q.Y. acknowledges a National Science Foundation Graduate Research Fellowship (DGE 1106400). N.S.G. acknowledges an Alfred P. Sloan Research Fellowship, a David and Lucile Packard Foundation Fellowship for Science and Engineering, and a Camille and Henry Dreyfus Teacher-Scholar Award.

Author contributions: MD designed and built the setup with QY. MD and HLW prepared samples and collected the data. MD analyzed the data. NSG supervised the research. MD and NSG wrote the manuscript with input from all authors.

Competing interests: The authors declare no competing interests.
1. Detailed description of the stroboSCAT setup

Our implementation of stroboSCAT is illustrated in Figure S1. For all data shown in the text, the light sources used are two laser diodes (LDH-D-C-440 for the pump and LDH-D-C-640 for the probe, PicoQuant, with center wavelengths 440 and 635 nm, respectively) driven by the same laser driver (PDL-828-S “SEPIA II” equipped with two SLM 828 driver modules and a SOM 828-D oscillator, PicoQuant). For the experiments shown in the text, we use a base laser repetition rate of 2 MHz, with the pump modulated at 660 Hz (every 3030 pulses), and the pump-probe delay times are controlled using the electronic delay capabilities of the driver with 20 ps resolution. We verified the calibration of the ‘coarse’ and ‘fine’ adjustments of the diode driver electronic delays using a computer-controlled mechanical translation stage (Newport) in a standard pump-probe geometry for delay times < 2 ns, and using an oscilloscope for delay times > 2 ns. We note that diodes and repetition rates are easily interchangeable for different experimental configurations. For short-time dynamics (<400 ps), diode afterpulsing can affect the accuracy of the measurements when using large diode powers. Therefore, care must be taken to minimize diode powers at the source, i.e. by reducing the driver current, rather than using neutral density filters in the beam paths. The resulting pulse FWHM are ~100 ps.

Both pump and probe are spatially-filtered through 20 µm pinholes (SF) and telescoped to ~6 mm and 1 mm beam diameters, respectively, before entering the microscope. The two beams are combined using a longpass filter (LP, DMLP505, Thorlabs) and directed to a home-built microscope of very similar design to the microscope body detailed in Ortega Arroyo et al. A f=300 mm wide-field lens (WFL) is inserted in the probe beam path upstream of the LP to focus the beam in the back focal plane of the objective, resulting in wide-field illumination (~5-60 µm depending on the beam size prior to the WFL) of the sample. A 50/50 beamsplitter (BS) reflects the pump and probe light into a high numerical aperture (1.4 NA) oil-immersion objective (Leica HC PL APO 63x/1.40NA) and onto the sample, resulting in an overlapped confocal and widefield illumination, respectively. Probe light reflected from the sample-substrate interface as well as scattered from the sample are collected through the same objective. The light transmitted through the beamsplitter is focused onto a charged metal-oxide semiconductor (CMOS) detector (PixeLINK PL-D752, equipped with the Sony IMX 174 global shutter sensor) using a f=500 mm lens placed one tube length (200 mm) away from the back focal plane of the objective. The total magnification is 63 x 500 /200 = 157.5. On square pixels of 5.86 µm this magnification corresponds to 37.2 nm/pixel. One longpass (FEL550, Thorlabs) and one bandpass (FLH635-10, Thorlabs) filter are used to filter out pump light in the stroboSCAT configuration. For widefield emission, other appropriate emission filter arrangements are used for any given sample. Optional half- or quarter-waveplates are used to control the polarization of pump and probe beams in polarization-sensitive measurements, such as for TIPS-pentacene described in the main text. The aperture (Ap) below the beamsplitter in Figure S1 is used...
to switch between reflection-only mode and interferometric scattering mode to ensure the contrast is due to a change in the scattering cross-section (Figure S3). A 3 mm beam stop can also be inserted at the same position as Ap to switch to darkfield backscattering microscopy (Figure S3). Although autofocusing capabilities as detailed in reference 1 were incorporated in the instrument, we found that stroboSCAT measurements are rapid enough and our microscope stable enough that autofocusing was not necessary, provided temperature fluctuations are minimal. Shutters are used to block pump and probe light (if desired) during program overheads to minimize sample exposure. The use of electronic delays & modulation, as well as a widefield probe, results in no moving parts in the setup (apart from optional shutters), leading to an extremely stable and compact (<1 m²) setup, with system realignment needed only once every 2 months with daily use.

Figure S1. Schematic of the stroboSCAT setup. Laser diodes synchronized through a single oscillator/laser driver are used for pump and probe, using driver electronics to delay the probe with respect to the pump. After passing through spatial filters (SF), the beams are combined with a longpass filter (LP) before reflecting off a 50/50 beamsplitter (BS) into the objective (obj). The pump is sent collimated into the objective while the probe is focused in the back focal plane of the objective to result in confocal and widefield excitation spots, respectively. Light reflected from the sample-substrate interface or scattered from the sample is collected, spectrally filtered (through a longpass and bandpass filter, BP) and focused onto a detector (CMOS). An aperture (Ap) may be used block the scattered light and image primarily normally-reflected light. Alternatively, a 3 mm beam stop can be inserted instead of Ap to block normally-reflected light and only image scattered light.

To trigger and synchronize the CMOS camera to the pump modulation rate, we use a phased dual-channel function generator to provide a 660 Hz TTL trigger signal to the CMOS and a synchronized 330 Hz trigger to the “Aux in” port of the laser driver. The latter starts each driver sequence that comprises 3030 pump pulses and 6060 probe pulses, both at a 2 MHz repetition rate. With the CMOS triggered at 660 Hz (and total exposure time set at 1.3 ms, averaging 2600 probe shots for each frame), consecutive images correspond to (1) probe with pump ON and (2) probe with pump OFF. The ratio pump ON/pump OFF for each consecutive pair is computed, and the ratio is averaged over 1000-3500 image pairs (total time with program overheads ~ 4-15 s per delay per scan for a full stroboSCAT image), depending on the signal-to-noise ratio (SNR) of the measurement. Averaged pump OFF images (iSCAT) are simultaneously recorded at each time delay. To be able to record images at 660 Hz we reduce the region of interest to 192x192 pixels, i.e. ~ 7 x 7 µm, though faster cameras could allow even larger fields of view.
The only image processing used is 2x2 pixel binning prior to Gaussian fitting (see Section 3 below). The stroboSCAT images shown in the text are raw, as-acquired images prior to 2x2 binning, and usually cropped to ~ 4 x 4 μm to emphasize the differential signal of interest. In principle, one could subtract negative-time delay stroboSCAT images for additional background subtraction, but we found this to have no effect on the fitting accuracy due to large signal-to-background ratio. Setup automation and data acquisition are implemented in LabVIEW 2014 64-bit. Data analysis and plotting is performed using a combination of imageJ (Fiji)\textsuperscript{6,7}, MATLAB and OriginPro.

The laser diodes provide high stability (<0.1% rms) and modularity in terms of repetition rates (single shot – 80 MHz), electronic delays (20 ps – 2 ms) and pulse sequencing, and fast warm-up times (<10 minutes from turning on) at the expense of time resolution compared to ultrafast lasers. We note that for interferometric contrast, the coherence length of the light source must be greater than the path difference between the scattered and reflected fields\textsuperscript{1}. However, very large coherence lengths are undesirable as they can lead to interference among many optical elements, thus degrading image quality\textsuperscript{8}. With a 2 nm spectral FWHM of the probe diode, we estimate a coherence length of ~40-60 μm depending on the medium’s refractive index – much larger than the path difference for any films or crystals deposited on the substrate, but not large enough to lead to much interference from optical elements in the beam path. Ultrafast lasers with >30 nm spectral bandwidths (<2 μm coherence length) are in principle still coherent enough for many samples to further enhance stroboSCAT time resolution. The use of ultrashort pulses for pump excitation is not affected by coherence length constraints. Nevertheless, another advantage of using pulsed diodes is the low peak powers needed compared to highly impulsive (<100 fs) excitation for the same amount of overall excited state population. For short-pulse excitations, multi-photon effects, sample damage and heating must be carefully taken into consideration. For example, at the typical GW/cm\textsuperscript{2} peak powers used in many ultrafast pump-probe experiments, carrier temperatures in semiconductors can reach ~10\textsuperscript{5} K\textsuperscript{9,10}, leading to the observation of hot-carrier dynamics\textsuperscript{10,11} over several hundred picoseconds that we did not observe in our experiments using peak powers that are three orders of magnitude lower.

2. stroboSCAT contrast mechanism

In iSCAT, high sensitivity is achieved through interference of the scattered light of interest from the sample with light reflected at the substrate-sample interface (e.g. coverslip-sample interface). The light intensity reaching the detector, $I_d$, can be described as\textsuperscript{1}:

$$I_d = E_n^2 [r^2 + |s|^2 + 2r|s|cos\phi]$$

where $E_n$ is the incident electric field, $r$ is the amplitude of the reflection coefficient at the interface, $s$ is amplitude of the scattering coefficient of the object of interest, and $\phi$ is the phase difference between scattered and reflected light. The scattering cross-section scales with the particle size raised to the third power, so the $|s|^2$ term, which is usually the signal of interest in dark-field microscopy, scales with particle size raised to the sixth power, contributing very little to the overall signal for scatterers <50 nm. However, the interferometric cross term scales with $|s|$ rather than $|s|^2$, and is amplified by the reflection term $r$. This term thus dominates for small particles and allows for extremely high sensitivity measurements to be made by simply increasing the incident electric field strength. Furthermore, $\phi$ can be expanded into\textsuperscript{12,13}:

$$\phi = \phi_{gouy} + \phi_{scat} + \frac{4\pi zn}{\lambda}$$
where $\phi_{\text{gouy}}$ is the Gouy (focusing) phase difference between scattered and reflected light, which is constant (typically tuned to $-\pi < \phi_{\text{gouy}} < -\pi/2$ in iSCAT for maximum contrast\textsuperscript{14}, which we apply in stroboSCAT too) for a fixed objective-sample distance, $\phi_{\text{scat}}$ is the scattering phase (related to the material’s complex refractive index; $\phi_{\text{scat}} \approx 0$ for off-resonant probing), $z$ is the object-interface distance, $n$ is the refractive index of the medium, and $\lambda$ is the illumination wavelength. Thus the relationship $\phi \propto z$ allows for three dimensional contrast. For the MAPbI\textsubscript{3} films in Figure 3 of the main text, $n(635 \text{ nm}) = 2.6$, leading to a $\pi$ phase flip every 60 nm, which is similar to the pump and probe 1/e penetration depths (50-70 nm).

In stroboSCAT, the differential contrast is defined as:

$$\frac{I_{\text{pumpON}} - I_{\text{pumpOFF}}}{I_{\text{pumpOFF}}} = \frac{I_{\text{pumpON}}}{I_{\text{pumpOFF}}} - 1 \approx \frac{2\cos\phi(|s_{\text{pumpON}}| - |s_{\text{pumpOFF}}|)}{r + 2|s_{\text{pumpOFF}}|\cos\phi}$$

assuming that $|s|^2 \ll r|s|\cos\phi$ (Born approximation) and that $r$ does not change significantly between pump ON and pump OFF images (confirmed using the aperture Ap, Figures S1 and S3). Additional assumptions include that the $\sim \pi$ Gouy phase difference between scattered and reflected light dominates the scattered phase contribution to $\phi$, such that the $\cos\phi$ term is virtually identical for the pump ON and pump OFF cases and is approximately equal to -1 for processes occurring at the sample surface. When carriers channel deeper into the sample, however, the depth-dependent pump ON contribution to the relative phase, $\cos(4\pi \gamma z/\lambda)$, modulates the first term in the differential contrast expression above, enabling retrieval of depth-dependent information. The denominator can further be simplified to $r$, since $r \gg 2|s_{\text{pumpOFF}}|\cos\phi$. Thus, the contrast is proportional to the change in the scattering cross-section between the material in the presence vs. absence of excited state species, which in turn is directly proportional to the change in polarizability (or refractive index) of the material between unpumped and pumped states. Overall, stroboSCAT benefits from the elegance, sensitivity and 3-dimensional contrast achievable with iSCAT, but expands it to the entirely different realm of ultrafast energy flow.

3. Data analysis

Following 2x2 binning of the raw stroboSCAT images, several strategies can be used to extract the diffusivities. For isotropic diffusion (e.g. perovskite single crystals), we plot the line profile for each time delay along any given axis, integrating across 4 pixel-wide rectangular regions. The resulting profile is fitted with a Gaussian function for each time delay, as described in more detail further below. For anisotropic diffusion (e.g. TIPS-pentacene), the same strategy is used for both long and short diffusion axes.

The Gaussian function used to fit normal spatial distributions is:

$$y(t) = A(t) * \exp \left( -\frac{(x - x_c)^2}{2\sigma^2(t)} \right)$$

where $A(t)$ is a pre-exponential factor dependent on the contrast magnitude at each time delay $t$, $x_c$ is the center position, and $\sigma(t)$ is the Gaussian standard deviation for each time delay.

As detailed in Akselrod et al.\textsuperscript{15}, using the property that the variance of convolved Gaussians are additive, the solution to the diffusion equation in one dimension can be expressed as:

$$\langle x(t)^2 \rangle = \sigma^2(t) = \sigma^2(0) + 2Dt$$

4
where \( \langle x(t)^2 \rangle \) is the mean square displacement, \( \sigma^2 \) is the variance of the population distribution at any given time, and \( D \) is the diffusion coefficient. Thus, for ordered systems,

\[
D = \frac{\sigma^2(t) - \sigma^2(0)}{2t}.
\]

A more generalized form of the 1-dimensional diffusion equation applicable to both ordered and disordered systems can be written as:

\[
\sigma^2(t) - \sigma^2(0) = 2D_0 t^\alpha
\]

to account for subdiffusive transport behavior in disordered systems that exhibit a distribution of site energies and trapping, where \( \alpha < 1 \), or superdiffusive (ballistic) transport in systems where the time between species scattering events is long compared to observation times, where \( \alpha > 1 \).

We note that the variance obtained from Gaussian fitting of the intensity profile in stroboSCAT images is strictly speaking a convolution of the spatial distribution of excited species with the point spread function (PSF) of the system, which itself is a convolution of the individual pump and probe PSFs as well as that of the detector. However, since the latter three are invariant over time, they do not contribute to the difference signal \( \sigma^2(t) - \sigma^2(0) \).

For heterogeneous, anisotropic diffusion, one possibility is to plot a radial profile averaged over all angles and fit it with a half-Gaussian to obtain an average intensity distribution. To obtain plots like in Figure 4a of the main text, the radial distribution is instead split into 10 to 30 degree slices and the intensity distribution of each slice is measured (the intensity at any given distance from the central point is the integrated intensity of the pixels over the arc bounded by the slice). However, when trapping occurs, for example at grain boundaries, the carrier population is not normally distributed and thus cannot be accurately fit with a Gaussian function. In these circumstances, we measure the distance from the center of the radial distribution at which the population drops to \( 1/e \), and then convert the extracted half-width at \( 1/e \) value (\( w \)) to a Gaussian standard deviation using the relationship \( \sigma = \frac{w}{\sqrt{-2 \ln(I_T)}} \), where \( I_T \) is the chosen Gaussian intensity threshold (i.e. \( 1/e \) in this case), assuming a normal distribution. Section 8 details our simulations of depth-dependent heterogeneous diffusion using finite element analysis, providing a more quantitative analysis of phase-sensitive stroboSCAT images in complex media.

4. Sample preparation

Sample substrates: all substrates are 22 x 22 mm or 24 x 50 mm VWR #1.5 glass coverslips. Every substrate is subjected to an extensive cleaning procedure as follows: 15 min sonication in a 2% Hellmanex solution in NANOpure deionized water, followed by several quick rinses in NANOpure deionized water; 15 min sonication in NANOpure deionized water; 10 min sonication in acetone; 10 min sonication in isopropyl alcohol; immediately dried under a flow of filtered nitrogen; and finally cleaned with an \( O_2 \) plasma for 3 minutes in a reactive ion etch chamber.

Reagents: All reagents were used as received without further purification. Methylammonium bromide (MABr, GreatCell Solar); methylammonium iodide (MAI, GreatCell Solar); Cesium bromide (CsBr, Alfa Aesar); lead bromide (PbBr\(_2\), Alfa Aesar); lead iodide (PbI\(_2\), Alfa Aesar); lead chloride (PbCl\(_2\), Alfa Aesar); lead acetate trihydrate (Pb(Ac)\(_2\), Sigma-Aldrich); 6,13-Bis(triisopropylsilyl ethynyl)pentacene
(TIPS-Pentacene, Sigma-Aldrich); Trichloro(phenethyl)silane (TPS, Sigma-Aldrich); poly(methyl methacrylate) (PMMA, $M_w=120,000$, Sigma-Aldrich).

All solvents are purchased from Sigma-Aldrich.

Sample handling: All samples apart from Silicon and perovskite single crystals are prepared in a sealed glovebox with nitrogen atmosphere and with <2ppm $O_2$ and $H_2O$. Once prepared, the samples are sealed between two substrates using epoxy (EPO-TEK) in the glovebox to protect them from water and oxygen exposure during measurements. For atomic force microscopy measurements on thin films, another sample is prepared consecutively under the same conditions and using the same solution, but is not sealed between the two substrates and is measured immediately after preparation. Single crystals are all grown at ambient conditions. Once the crystals are grown, they are brought into the glovebox, placed on clean substrates, and 200 µL of a 40mg/mL solution of PMMA in chloroform is dropcast on the crystals to keep them in place and prevent exposure to oxygen and moisture during measurements.

Metal-halide perovskite single crystals: MAPbBr$_3$ single crystals were prepared according to a published procedure using antisolvent vapor diffusion$^{16}$. Briefly, a 1:1 molar ratio, 0.2 M solution of PbBr$_2$/MABr was prepared in N,N-dimethyl formamide (DMF). The solution was then filtered using a 0.2 µm PTFE syringe filter. 2 mL were placed in a clean 4 mL vial, which was placed inside a larger scintillation vial filled with dichloromethane. The large vial was sealed and crystals were left to grow for 1 week, resulting in hyperrectangular crystals of dimensions ~ 3 x 3 x 1 mm.

CsPbBr$_3$ single crystals were grown using antisolvent vapor diffusion according to a published procedure$^{17}$. The same procedure as that described for MAPbBr$_3$ was used, with a 1:1 molar ratio, 0.04 M solution of PbBr$_2$/CsBr in DMF and using nitromethane as antisolvent. The crystals were left to grow for 3 weeks, resulting in large hyperrectangular crystals of dimensions ~ 20 x 2 x 2 mm, which were cleaved before mounting on substrates for measurements.

MAPbBr$_3$ polycrystalline films were prepared by dissolving MABr and Pb(Ac)$_2$ in a 3:1 molar ratio in DMF with a final concentration of 0.5 M. The solution was spin-cast at 2000 rpm for 60 seconds. The films were subsequently annealed for 5 minutes at 100°C$^{18}$.

MAPbI$_3$ polycrystalline films were prepared using different published processing routes, described briefly below:

$Pb(Ac)_2$ precursor films$^{18}$ were prepared by dissolving MAI and Pb(Ac)$_2$ in a 3:1 molar ratio in DMF for a final concentration of 0.5 M. The solution was spin-cast at 2000 rpm for 60 seconds. The films were subsequently annealed for 5 minutes at 100°C.

$PbI_2$ precursor films$^{19}$ were prepared by dissolving MAI and PbI$_2$ at a 1:1 molar ratio at 200 mg/mL in DMF. The solution was spin-cast at 2000 rpm for 30 seconds. The films were subsequently annealed for 20 minutes at 100°C.

$PbCl_2$ precursor films$^{20}$ were prepared by dissolving MAI and PbCl$_2$ at a 3:1 molar ratio with final concentrations of 2.64 M and 0.88 M, respectively. The solution was spin-cast at 2000 rpm for 60 seconds. The films were subsequently left to dry for 30 minutes at room temperature in the glovebox, followed by annealing at 90°C for 150 minutes.
TIPS-pentacene was dissolved in toluene at 5mg/mL and filtered through a 0.45 µm PTFE filter. The substrates were treated by leaving to soak overnight in a petri dish with a solution of 190 µL TPS in 100 mL toluene, then rinsed with toluene and dried prior to deposition. The TIPS-pentacene solution was then spin-cast at 250 rpm, and then solvent-vapor annealed at 60°C in a toluene-saturated atmosphere for 24 hours.

Silicon wafers were prime-grade P-type, boron-doped wafers purchased from WaferNet Inc., used without further modification.

5. Current system resolution

Figure S2. (a) pump reflection from a glass substrate imaged on the CMOS camera, exhibiting a Gaussian profile with a FWHM of 306 nm. (b) widefield probe PSF imaged using a 40 nm gold nanoparticle. The central part of the PSF corresponds closely to the expected diffraction-limited Gaussian. (c) Gaussian peak amplitude as a function of pump-probe time delay at early times for a stroboSCAT experiment on TIPS-Pentacene. The instrument response function of the system is estimated to be ~240 ps.

As shown in Figure S2, the 440 nm pump beam profile has a FWHM of 306 nm, which is ~ twice the diameter of a diffraction-limited spot. The total system spatial resolution is ~ \( \sqrt{306^2 + (635/2.8)^2} = 381 \) nm. Using a diffraction-limited pump could improve the resolution to a best-case scenario (with these wavelengths) of ~276 nm. We opted for a non-diffraction-limited beam by underfilling the objective in order to avoid polarization scrambling in the focal plane. The measured probe PSF (Figure S2b) is used in the simulations in Section 8.
The system temporal instrument response function (IRF) is determined to be ~240 ps using a half-Gaussian to fit the signal rise-time in a stroboSCAT experiment on TIPS-pentacene (Figure S2c).

6. **Distinguishing scattering from normal reflection**

It is possible to separate scattered and illumination light near the back focal plane of the objective by making use of the fact that small scatterers (e.g. individual energy carriers, quantum dots, nanoparticles etc.) near a refractive index interface radiate the majority of photons at the critical angle determined by the interface\(^4.5.21\). The result is that the scattered field is distributed in directions primarily associated with a high numerical aperture of the objective\(^4\). Since widefield illumination only requires a very low numerical aperture, the spatial frequencies of the scattered light and illumination beam are well separated near the back aperture of the objective. Indeed, it has been shown in iSCAT experiments that the illumination beam can be attenuated with an appropriate partial reflector while transmitting the vast majority of the scattered field in order to increase the iSCAT contrast significantly\(^4.5\). Similarly, the normally-reflected light can be entirely blocked, resulting in a sensitive darkfield backscattering microscope\(^2\).

To verify that the same separation of spatial frequencies is present in stroboSCAT, and to confirm the signal source is scattering from a collection of small particles (and not just a change in the reflectivity \(r\) of the interface), we introduced an aperture near the back aperture of the objective (Figure S1) to be able to interchange between stroboSCAT and normal reflectivity modes of imaging.

![Aperture diagram](image)

**Figure S3.** stroboSCAT contrast for TIPS-pentacene at 0 ns delay. The images from left to right show how the contrast changes as high spatial frequencies of the scattering field are progressively filtered out using an aperture near the back aperture of the objective.

Figure S3 shows the effect of spatially filtering the scattered field only while the normally-reflected illumination field is fully transmitted. The stroboSCAT signal magnitude reduces and the spatial extent of the signal on the detector plane increases as high spatial frequencies are filtered out. These experiments indicate that the scattered field emitted toward high-NA associated directions is indeed responsible for the observed signal.

Furthermore, a 3 mm beam stop attached to a thin wire was inserted to block the normally-reflected beam while transmitting the scattered field only\(^2\). Using the same experimental conditions, we were unable to observe any signal above noise on the detector. In contrast, dust particles or other strongly-scattering objects switch from dark contrast on a bright background to bright contrast on dark background, as expected for darkfield microscopy.

The same control measurements were performed on all samples, giving identical results. Taken together, these observations indicate that the interferometric cross-term dominates the differential signal.
magnitude, i.e. \( s^2 \ll r \cos \phi \), and the reflectivity \( r \) does not change significantly between pumped and unpumped states. Thus, darkfield microscopy or normal transient reflection microscopy are not able to achieve the same sensitivities as stroboSCAT.

7. Supporting experimental data

All reported injected energy carrier densities, \( n_0 \), are calculated as \( n_0 = j \alpha \), where \( j \) is the peak pump fluence in photons/cm\(^2\), and \( \alpha \) is the absorption coefficient. Peak photon fluence is calculated from peak energy fluence, which is defined here as \( 2E/\pi r^2 \), with \( E \) being the pulse energy and \( r \) being the beam radius at \( 1/e^2 \). For each sample, a pump-power dependence over several time delays is performed in order to ensure that the rate of decay of the stroboSCAT signal peak amplitude is power-independent over the range of powers used. In this way we ensure that many-body effects such as Auger recombination do not contribute significantly to the determined diffusivities. Using higher powers may lead to incorrect estimations of the diffusion coefficient as the population distributions approach flat-top profiles rather than Gaussian profiles, which, if fit with a Gaussian function, will appear as erroneously large distribution widths\(^{19} \). For TIPS-Pentacene, power-dependent behavior is non-trivial and discussed in more detail in Figure S11.

7.1. Silicon

Figure S4. stroboSCAT time series on a p-doped Si wafer. Just before 0 ns pump-probe delay, the signal exhibits negative (dark) contrast, which rapidly expands with time. At 0 ns pump-probe delay, a positive-going contrast appears in the center of the distribution, indicating a different species is formed rapidly. Double-Gaussian fitting of the signal allows extracting the diffusivities for each species. The negative Gaussian expands at a rate of \( 35 \pm 8 \) cm\(^2\)/s and the positive Gaussian expands at a rate of \( 0.6 \pm 0.2 \) cm\(^2\)/s (Figure 1). These are close to reported values for electron\(^{22} \) and thermal\(^{23} \) diffusivities in Si. We therefore attribute the negative (dark) contrast to photogenerated electrons, and the positive (bright) contrast to heat deposited in the lattice through relaxation of excess energy from above-bandgap excitation as well as electron-electron, electron-hole and electron-phonon scattering that happen primarily in the center of the carrier distribution, where the carrier density is largest. Note that this is the only sample where fitting errors are larger than the variation from dataset to dataset, primarily due to fast-diffusing carriers, low contrast and the need for double-Gaussian fitting. Fluence is 0.5 mJ/cm\(^2\) (\( n_0 \approx 2 \times 10^{19} \) cm\(^{-3}\))\(^{24} \).
7.2. CsPbBr$_3$

Figure S5. stroboSCAT time series on a CsPbBr$_3$ single crystal. The extracted diffusivity from this dataset is 1.00 ± 0.08 cm$^2$/s (Figure 1). The average and standard deviation across 6 datasets and 2 crystals are 1.0 ± 0.2 cm$^2$/s. Fluence is 21 µJ/cm$^2$ ($n_0 \approx 4 \times 10^{18}$ cm$^{-3}$)$^{25}$.

Figure S6. stroboSCAT contrast difference at 0 ns pump-probe delay at a fluence of 10 µJ/cm$^2$ for MAPbBr$_3$ vs. CsPbBr$_3$ single crystals. The contrast magnitude is lower by a factor of 2.7 in CsPbBr$_3$ despite both systems having similar absorption coefficients and both being probed with below-bandgap, off-resonant light. The extent to which contrast magnitude can be used to gain information on electron-phonon coupling in these different systems will be the subject of future investigations.
7.3. MAPbBr₃ polycrystalline films

Figure S7. stroboSCAT time series on a MAPbBr₃ polycrystalline film. Note that background contributions due to sample vibrations/drift during acquisition are larger for heterogeneous samples than for samples that scatter homogeneously. The extracted diffusivity from this dataset is 0.15 ± 0.02 cm²/s. The average and standard deviation across 5 datasets are 0.16 ± 0.05 cm²/s. Fluence is 10 µJ/cm² \( (n_0 ≈ 2 \times 10^{18} \text{cm}^{-3}) \).²⁶

7.4. TIPS-Pentacene

Figure S8. The iSCAT images of TIPS-pentacene crystalline domains shown in Figures 2b of the main text are filtered using a Fourier bandpass, allowing to remove stripes from probe light diffraction off of crystalline interfaces in the sample. The diffraction stripes are a consequence of using widefield illumination. The raw images are shown here at the top. Scale bars are 1 µm.
Figure S9. Anisotropic intra-grain diffusivity in TIPS-Pentacene. Diffusivity along the long axis (red) is approximately 6 times larger than along the short axis (blue), as expected for anisotropic π-stacked systems\textsuperscript{15,27}.
Figure S10. Additional datasets on TIPS-Pentacene in three crystalline domains and at two GBs. stroboSCAT images are shown on the left at 0 and 8 ns time delays. In the middle column, corresponding iSCAT (pump OFF) images at the probe polarizations used for each dataset are shown. On the right, a larger field-of-view image is used to capture the three domains in a single image at a given polarization – note that the contrast for each crystalline domain in iSCAT (pump OFF) images switches between bright and dark depending on the probe polarization used. The middle grain appears somewhat out-of-plane (i.e. the $c$-axis is not perpendicular to the substrate plane), as evidenced by a non-circular profile of the excitation spot at 0 ns in the stroboSCAT image, which we attribute to projection distortion. This non-planar orientation of the crystalline domain was observed in around 20% of the domains investigated in these films. For these datasets and those shown in the text, the pump was circularly polarized. When investigating GBs, the probe polarization is set to equalize contrast across grains, as shown explicitly in the iSCAT images above. We tested the validity of this approach by verifying that similar results were obtained with a circularly-polarized probe both in grains and at GBs, although the signal-to-noise ratio was poorer when using a circularly polarized instead of linearly polarized probe beam.
Figure S11. Population expansion plots for the data in Figure S10. A subdiffusive model is used to fit the data and extract an effective $D_0$ and to compare among grains and GBs. Due to the larger noise at GBs and apparently linear diffusive behavior, we used a linear model there instead to avoid over-fitting.

Figure S12. In TIPS-Pentacene, early-time dynamics are dictated by singlet-fission into two triplets and the reverse process of triplet fusion into a singlet, which affects the rate of exciton migration since singlets diffuse faster than triplet excitons$^{28,29}$. The combination of this interplay with singlet-singlet annihilation gives rise to nonlinear diffusive dynamics for as long as triplets are strongly bound – up to nanoseconds$^{30}$, as seen in the middle panel. To eliminate singlet-singlet and free triplet-triplet annihilation and concentrate on intrinsic singlet-triplet interchange, our measurements are taken at 147 fJ (140 uJ/cm$^2$ peak fluence), as we detect no significant changes in the peak amplitude decay between 74 and 147 fJ (the left panel plots the normalized peak Gaussian amplitudes of the stroboSCAT signal). At higher fluences, faster decay of the peak amplitudes at early times is observed, resulting in faster apparent diffusion. At long times (>5 ns), once all triplets are fully separated, linear diffusivities of $3 \times 10^{-3}$ cm$^2$/s are observed for all fluences used (right panel), which we assign to free triplet diffusion in TIPS-pentacene.
7.5. MAPbI$_3$

Figure S13. Example AFM and confocal images for the three MAPbI$_3$ films studied, allowing to extract approximate grain sizes for each sample. AFM and confocal images are not from the same sample areas.

Figure S14. Absorption spectra, emission spectra, and emission lifetime for MAPbI$_3$ films prepared from Pb(Ac)$_2$ (black), PbI$_2$ (red), and PbCl$_2$ (orange) precursors. The absorption spectra are baselined by subtracting the transmission changes due to scattering and reflectance to facilitate comparison between films. Emission spectra and lifetimes are measured using 470 nm excitation at ~0.1 µJ/cm$^2$ on a FluoTime 300 instrument (PicoQuant). The curves overlaid on emission decay traces correspond to stretched exponential tail fits $A \times \exp(-t/\tau)^\beta$ with parameters $\tau = 276, 24, 379$ ns and $\beta = 0.88, 0.48, 0.74$ for films made from Pb(Ac)$_2$, PbI$_2$, and PbCl$_2$ precursors, respectively. The decay lifetimes correspond closely to those reported for related preparation protocols.$^{20,31,32}$

Figure S15. Illustration of spot-to-spot heterogeneity within a single film of MAPbI$_3$ made with PbCl$_2$ precursor. Both the stroboSCAT time series and widefield emission show vastly different inter-grain connectivity patterns at each spot. Trapping times differ too, with some spots exhibiting population expansion up until 5 ns while others display expansion up until 50 ns. Good correspondence between widefield images and stroboSCAT images at late times confirms that stroboSCAT captures the full extent of carrier diffusion; however, some differences between widefield and stroboSCAT images at late times can arise if electron and hole transport are substantially different, for example due to preferential trapping of one species at GBs, since excess free carriers of one species will not give rise to photoluminescence, but will still change the polarizability of the medium. All excitation fluences are 10 µJ/cm$^2$ ($n_0 \approx 1.5 \times 10^{18}$ cm$^{-3}$)$^{33}$. 
Figure S16. Specific intra- and inter-grain connectivity patterns determine carrier diffusion pathways in large-grain MAPbI$_3$ (PbCl$_2$) films. Here we show stroboSCAT time series and widefield emission images when pumping at two slightly offset spots in the same region of the film. The gold and blue circles show where the initial distribution of free carriers are injected. The same circles are overlaid on the 5 ns images to allow spatially correlating the two images. The final carrier population distribution and contrast flips correspond almost perfectly, confirming that fast intra-grain transport and preferential inter-grain connectivities across depth- and lateral-dependent paths of least resistance through GBs define overall carrier transport pathways.

Figure S17. Pump-power-dependent diffusivities in MAPbI$_3$(Cl) films. Red and blue curves in (b) correspond to integrated intensity profiles delimited by the rectangles in (a). Results show a small, ~10% variation of carrier population distribution on average despite a 30-fold reduction in fluence. Lower excitation powers display slightly broader distribution profiles, likely an indication that slightly fewer carrier-carrier scattering events impede diffusion at early times in the low-fluence measurements. The small deviation confirms that high-order recombination terms do not contribute largely to the stroboSCAT measurements at the fluences used.
8. Simulations of depth-dependent carrier diffusion in polycrystalline films using the finite element method

We simulate depth-dependent charge diffusion in MAPbI$_3$(Cl) films using finite element analysis implemented in the MATLAB PDE toolbox. The parabolic diffusion equation is solved in a heterogeneous environment consisting of grains separated by abrupt grain boundaries. The code is implemented in a two-dimensional x-z (lateral-axial) plane. In brief, the simulations quantitatively reproduce the observed diffusion behavior and associated stroboSCAT contrast. The key aspect of the simulations is the inclusion of a depth-dependent diffusion coefficient at GBs. The model depends most sensitively on the depth at which the diffusion coefficient increases from ~0 at the surface to its intra-grain value. All simulation parameters are detailed in Section 8.1, and the results are further supported by additional datasets and simulations in Section 8.2. This last Section includes structural information correlated to stroboSCAT measurements in the same field of view to further constrain the model and confirm our interpretation: contrast flips in the stroboSCAT data on MAPbI$_3$(Cl) films occur specifically at GBs and indicate that when carriers encounter GBs, they cannot cross into neighboring grains at the film surface, instead moving deeper into the film, where GBs are not as resistive.

8.1 Simulation parameters and assumptions

The MAPbI$_3$(Cl) film thickness is 300 nm as measured by AFM. GBs are assumed to lie approximately perpendicular to the substrate plane. The films are assumed to be 1 grain thick (i.e. no GBs parallel to the substrate plane), as illustrated in Figure 3c of the main text. These assumptions are reasonable based on cross-sectional SEM measurements taken on MAPbI$_3$(Cl) films prepared using the same protocol$^{34}$. The GBs are simulated as 200 nm thick, which accounts for slightly diagonal orientations of the GBs. We choose 200 nm based on confocal fluorescence microscopy measurements that show occasionally completely dark GBs even though the image is convolved with a ~200-300 nm point spread function, implying that the effect of GBs is felt over a >150 nm region despite the fact that they may be far thinner.

For simulations with correlated structural measurements (Section 8.2), slight adjustments to the GB thickness are made in the simulation if they are determined to be larger than the diffraction limit in the confocal measurement. Von Neumann boundary conditions are assumed at all film edges, though the proportion of carriers reaching the lateral edges are negligible over the simulation time. Interparticle interactions are ignored, supported by the fluence-dependent measurements shown in Figure S17. A first-order rate constant for recombination is included (see below). The starting condition is an injected carrier density profile from the pump with a FWHM of 306 nm and exponentially decaying as a function of depth with a 1/e penetration depth of 60 nm.

The key simulation parameters are shown in Figure S18. First, the GBs are assumed to have depth-dependent resistive properties. This assumption is based on conductive-probe AFM measurements that show that the surface of GBs in MAPbI$_3$ films are infinitely resistive, but that carriers do cross grain boundaries, leading the authors to postulate that the resistivity of GBs decreases as a function of depth$^{35}$. While the depth-dependent resistive profiles can adopt many forms, and may be GB-dependent and film-dependent, we adopt the simple form shown in Figure S18a: an infinitely-resistive surface as previously measured using AFM, with a rapid drop-off to a value similar to the bulk resistivity. Note that the value that is varied in the simulations is the diffusion coefficient, related to resistivity $\rho$ through the Einstein equation, $D=kT/(q^2N\rho)$, for charge $q$ and charge number density $N$. The simulations qualitatively reproduce the data over a wide range of drop-off rate and final value for the diffusivity, but the onset of
the drop-off is well-constrained: carriers need to pass through the GB in the region of 40-80 nm below the surface to reproduce the signals we observe. Importantly, including depth-dependent resistive profiles at GBs is crucial to reproducing stroboSCAT data for every simulated dataset – the phase flips cannot be reproduced with any other parameters described herein, and we have never observed phase flips due to changes in the carrier density in these materials over 4 orders of magnitude in pump fluence.

Second, the recombination rate at the top and bottom surface of the films are assumed to be 10 times larger than in the bulk, based on multiple studies showing that surface recombination dictates carrier lifetimes in MAPbI₃ perovskites. The recombination rate profile shown in Figure S18b is determined based on the knowledge that surface contributions dominate photoluminescence decay with 400 nm excitation (~40-60 nm penetration depth). The simulation reproduces the experimental results over a wide range of parameters for the recombination rate profile vs depth.

Finally, after simulation carrier diffusion, the stroboSCAT contrast is reproduced by applying a contrast scaling term based on the phase sensitivity of iSCAT (see Section S2). A π phase shift, which occurs every λ/4n ≈ 60 nm, corresponds to a contrast flip from negative to positive. To account for the finite probe penetration depth of d = 67 nm, and the fact that probe photons that reach the detector upon scattering at a sample depth z pass through 2z of the material, we attenuate the simulated incident probe light using a damped cosine function: $-\cos(\Delta \phi) \cdot e^{-2z/d}$, where $\Delta \phi$ is the phase shift $\Delta \phi = 4\pi nz/\lambda$.

The negative sign accounts for the fact that the phase at the surface is $-\pi$ due to the Gouy phase (Section 2). Finally, once this scaling is applied, the contrast is integrated across the depth of the film to simulate the stroboSCAT signal, which is then convolved with the probe PSF (Figure S2b).

![Figure S18](image.png)

**Figure S18.** Depth-dependent simulation parameters: diffusivity (a), recombination rate (b), and contrast scaling due to interferometric phase sensitivity. See text in Section 8.1 for details.

### 8.2 Simulation results with structural correlation: confirming stroboSCAT contrast flips occur at GBs.

To confirm that tracing carriers in 3D using stroboSCAT provides structural information, we undertook measurements on a well-defined region in a MAPbI₃(Cl) film with grains that are clearly visible and separated in confocal fluorescence microscopy. The use of an optical method (rather than AFM or SEM) for structural correlation is necessary as the films need to be imaged on the same side as the probe is
incident, i.e. through the sample substrate, and in air- and moisture-free conditions. Figure S19 shows the region used for correlated measurements, with a well-defined central grain. A watershed algorithm in ImageJ is used to delimit the location of GBs.

Figure S19. Region in a MAPbI\(_3\)(Cl) film used for structurally-correlated stroboSCAT measurements.

Figure S20. Structurally-correlated stroboSCAT-confocal fluorescence measurements. (a) stroboSCAT time series with correlated widefield emission from confocal excitation. The overlaid cyan curves show the 4 most relevant grains taken from Figure S19. (b) Correlated scanning-beam confocal fluorescence and elastic scattering at 635 nm. (c) Experimental and simulated stroboSCAT data for different time delays through the line cut indicated by the horizontal red line in (a) and (b). The simulations use the GB positions through the line determined from the confocal image in (b).
Figure S20a shows the stroboSCAT data when exciting the large central grain. By overlaying the GB positions determined from confocal microscopy on the 0 ns and 5 ns frames, it is clear that the positive (light) contrast in stroboSCAT arises at the GB locations. The same picture as that described in Figure 3 of the main text emerges: as carriers approach GBs, the stroboSCAT contrast flips from negative to positive, indicating that carriers pass GBs only at locations below the film surface. Once carriers have crossed GBs, they again freely move in 3 dimensions within grains, thus restoring the negative contrast. Since the stroboSCAT signal is strongest near the illuminated surface (Figure S18c), where the contrast is negative, stroboSCAT gives rise to negative contrast within grains and positive contrast at GBs, clearly delineating the structure of these polycrystalline films.

These deductions are confirmed with the finite element diffusion simulations shown in Figure S20c and Figure 3d, which reproduce the signal almost quantitatively despite using a relatively simple model. In the simulations shown in Figure S20c, the positions of the GBs are constrained to those determined in confocal microscopy.

References
15. Akselrod, G. M. et al. Visualization of exciton transport in ordered and disordered molecular


